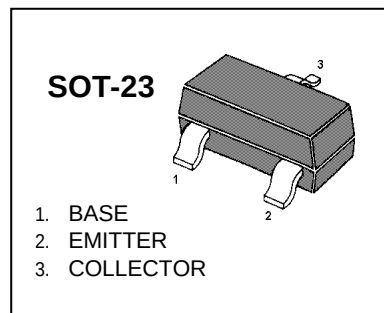


Plastic-Encapsulate Transistors

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation

MARKING: ZF



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	- 40	V
V_{CEO}	collector-emitter voltage	open base	-	- 40	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
I_C	collector current (DC)		-	- 2	A
I_{CM}	peak collector current		-	- 3	A
I_{BM}	peak base current		-	- 300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	-	300	mW
		$T_{amb} \leq 25^\circ\text{C}$; note 2	-	480	mW
T_{stg}	storage temperature		- 65	+150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		- 65	+150	$^\circ\text{C}$

Notes

1. Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tin plated, mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tin plated, mounting pad for collector 1 cm².

CHARACTERISTICS

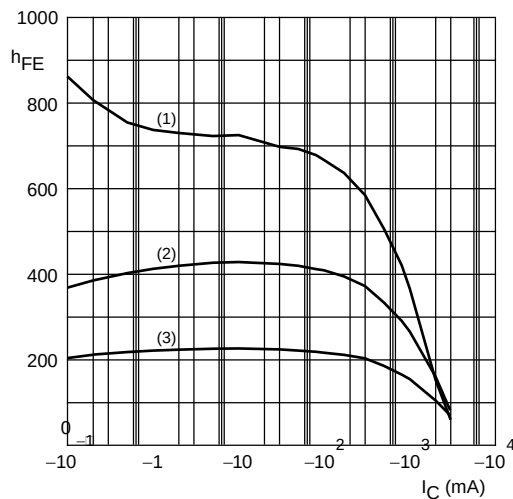
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0$	-	-	-100	nA
		$V_{CB} = -30\text{ V}; I_E = 0; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
I_{BEO}	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}$				
		$I_C = -100\text{ mA}$	300	450	-	
		$I_C = -500\text{ mA}$	260	350	-	
		$I_C = -1\text{ A}$	210	290	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-55	-100	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-70	-110	mV
		$I_C = -750\text{ mA}; I_B = -15\text{ mA}$	-	-140	-225	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	-	-140	-225	mV
		$I_C = -2\text{ A}; I_B = -200\text{ mA}$	-	-240	-350	mV
R_{CEsat}	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ note 1	-	160	220	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -200\text{ mA}$	-	-	-1.1	V
$V_{BE(on)}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	-	-	-0.75	V
f_T	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	100	200	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0;$ $f = 1\text{ MHz}$	-	23	28	pF

Note

- Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.

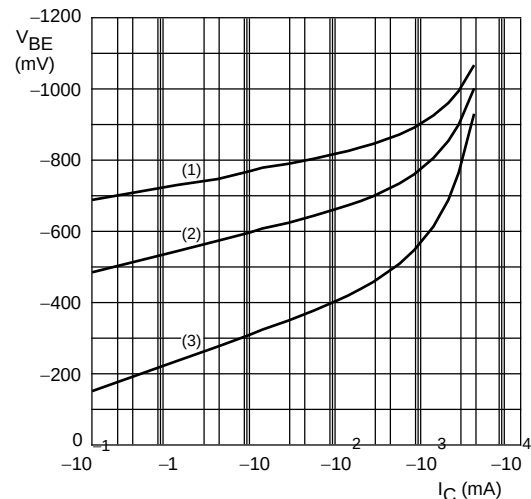
Typical Characteristics



$V_{CE} = -2\text{ V}.$

- $T_{amb} = 150\text{ }^{\circ}\text{C}.$
- $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- $T_{amb} = -55\text{ }^{\circ}\text{C}.$

Fig.1 DC current gain as a function of collector current; typical values.

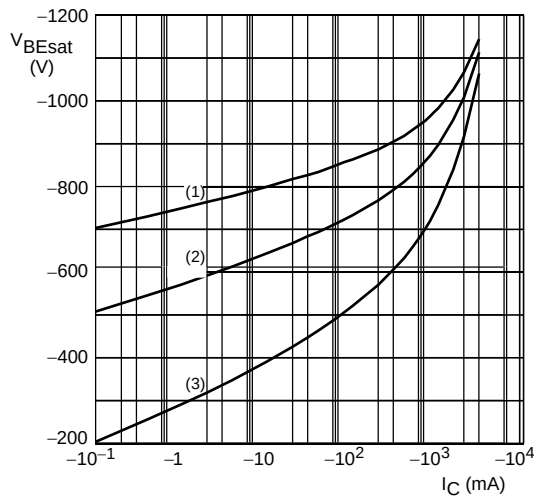


$V_{CE} = -2\text{ V}.$

- $T_{amb} = -55\text{ }^{\circ}\text{C}.$
- $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- $T_{amb} = 150\text{ }^{\circ}\text{C}.$

Fig.2 Base-emitter voltage as a function of collector current; typical values.

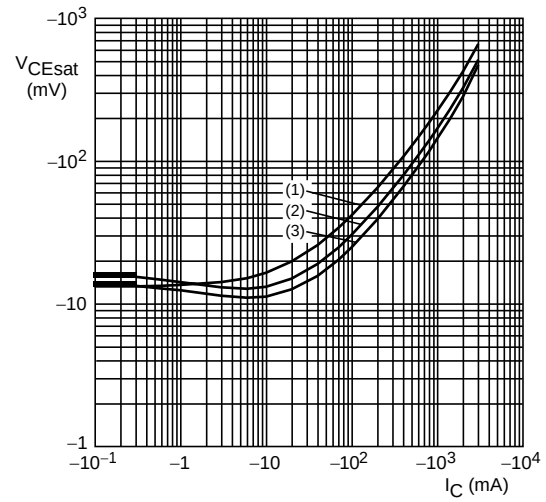
Typical Characteristics



$I_C/I_B = 20$.

- (1) $T_{amb} = -55\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = 150\text{ °C}$.

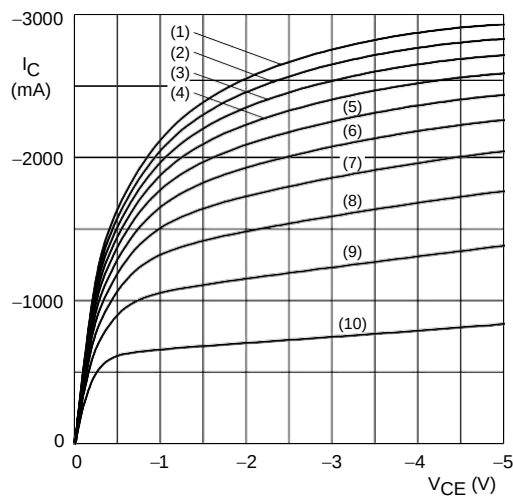
Fig.3 Base-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 20$.

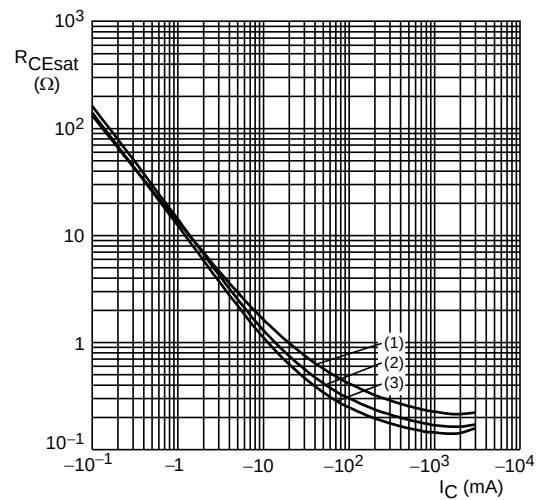
- (1) $T_{amb} = 150\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -55\text{ °C}$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



- (1) $I_B = -23.0\text{ mA}$.
- (2) $I_B = -20.7\text{ mA}$.
- (3) $I_B = -18.4\text{ mA}$.
- (4) $I_B = -16.1\text{ mA}$.
- (5) $I_B = -13.8\text{ mA}$.
- (6) $I_B = -11.5\text{ mA}$.
- (7) $I_B = -9.2\text{ mA}$.
- (8) $I_B = -6.9\text{ mA}$.
- (9) $I_B = -4.6\text{ mA}$.
- (10) $I_B = -2.3\text{ mA}$.

Fig.5 Collector current as a function of collector-emitter voltage; typical values.



$I_C/I_B = 20$.

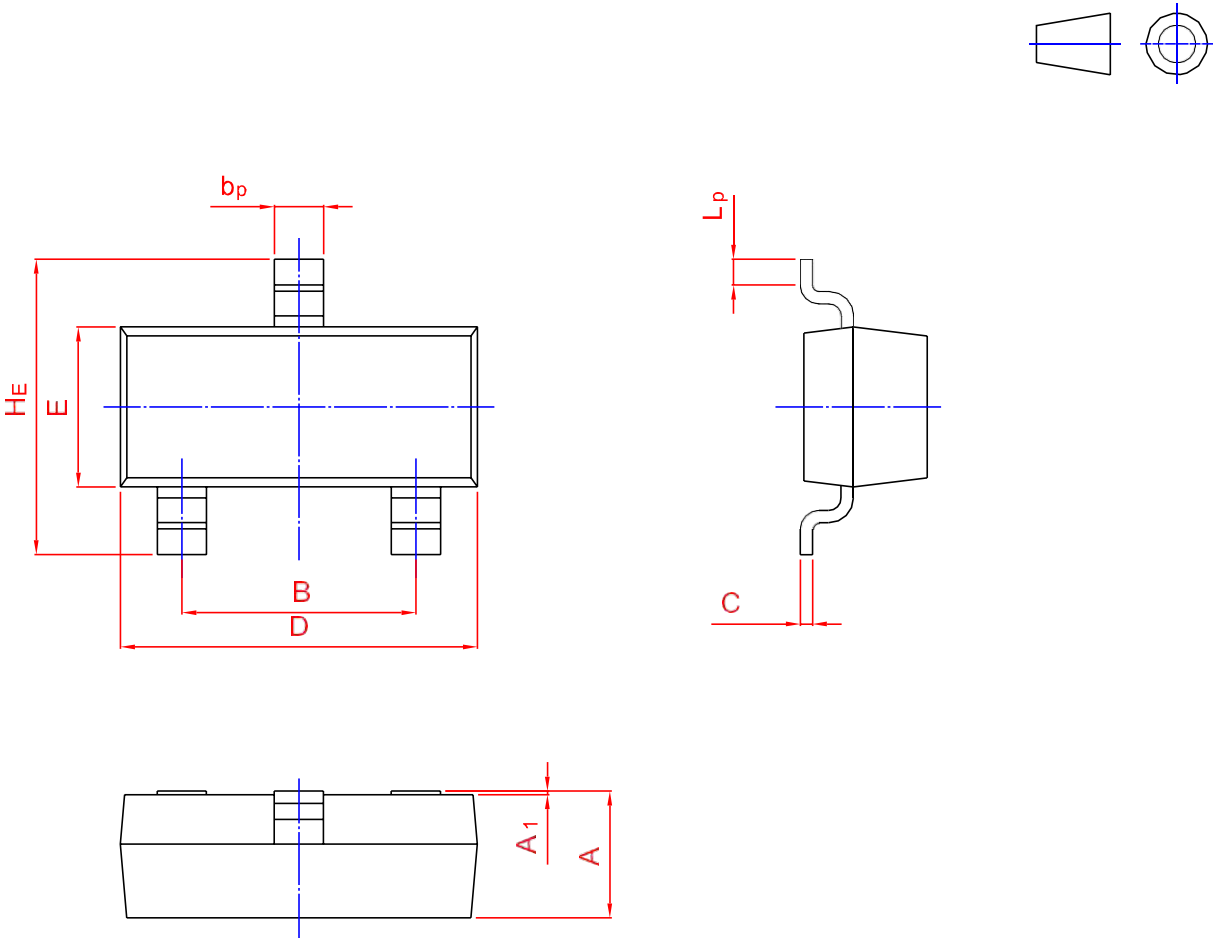
- (1) $T_{amb} = 150\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -55\text{ °C}$.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20